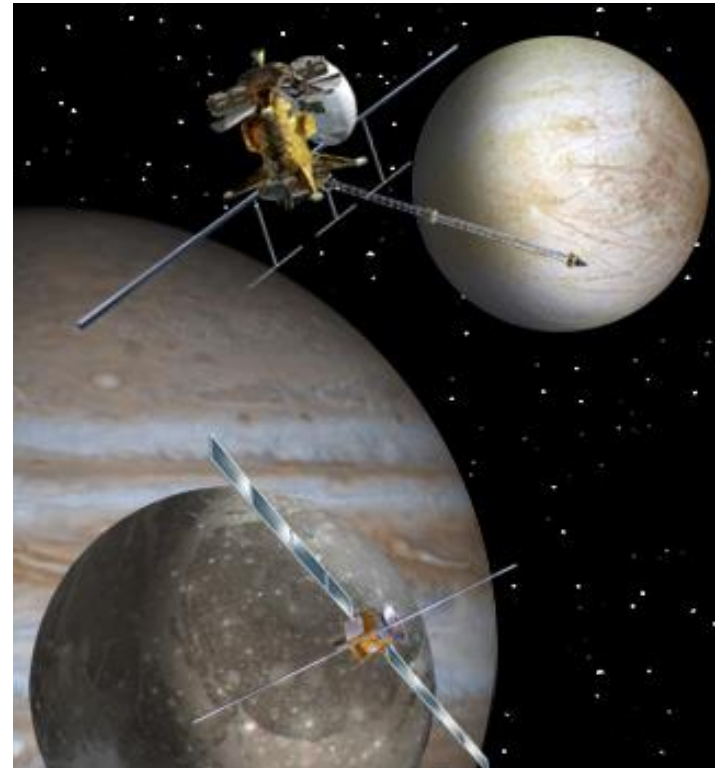


Technical Presentation

Jayasimha V. Bagalkote (ESR 5)
Seibersdorf Laboratories
Supervisor : Dr. Peter Beck

4th Annual ARDENT Workshop
22 – 26 Jun 2015, Prague



Artists` impression of JUICE mission Courtesy: ESA

CONTENT

1. e²RAD - **e**nergetic **e**lectrons **r**adiation assessment study for JUICE mission
2. ECI – **E**uropean **C**omponents **I**nitiative
 - Project Overview
 - Test candidates selected for testing
 - Results TID-Testing
 - Results SEGR-Testing
3. REDI – **R**adiation **E**valuation of **D**igital **I**solators
 - Project Overview
 - Test candidates selected for testing
4. Summary and Conclusions

What is JUICE?

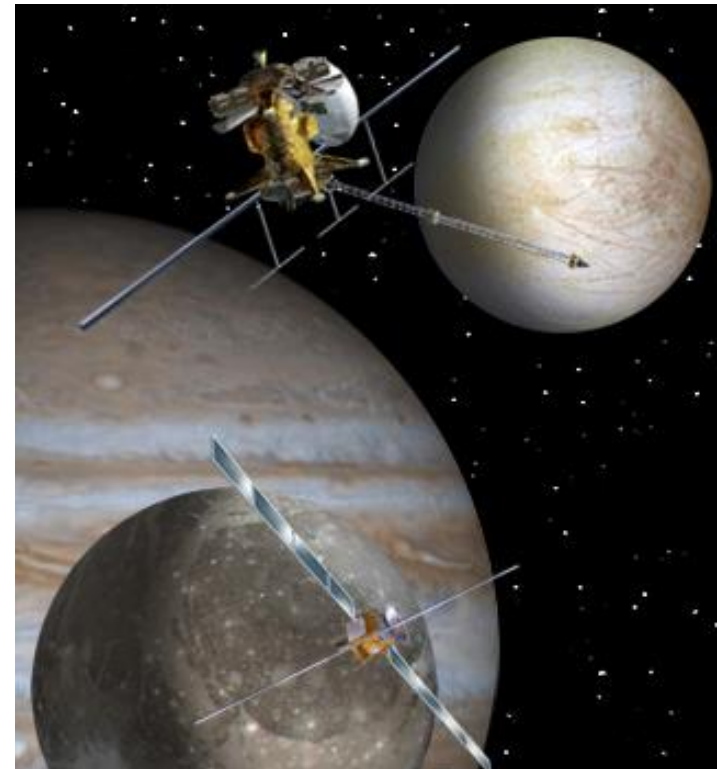
Jupiter ICy moons Explorer (JUICE) - ESA mission

Timeline:

- In 2022 - launch
- In 2030 - Jupiter, Ganymede, Callisto, Europa

Studies:

- Jupiter's atmosphere, magnetosphere, interaction with the 3 moons and Io
- Surfaces and interiors of the 3 moons, potential to host life



Artists` s impression of JUICE mission Courtesy: ESA

e²RAD Project

e²-RAD: energetic electrons radiation assessment study for JUICE mission

Objectives: To investigate shielding-performance of 2-layered Shielding set-ups with different Geometries and relative composition of High-Z and Low-Z materials.

- High-Z : Tantalum, Lead
- Low-Z material : Aluminum
- Major Dose contribution: trapped electrons
- Energy range: 5 MeV – 50 MeV

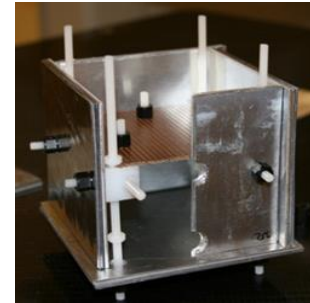


Fig 2: Box-shielding configuration

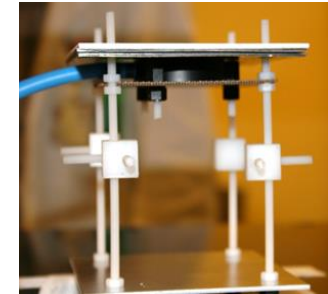


Fig 3: Plane-shielding configuration

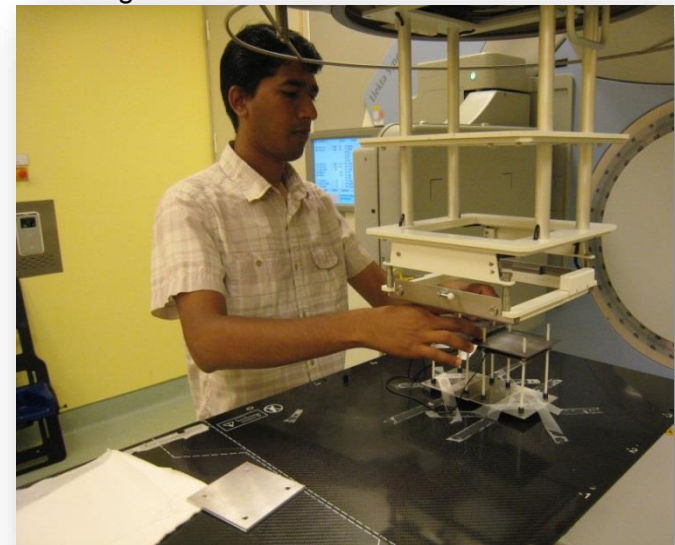


Fig : Experiments at LINAC facility, AKH-Vienna.

e²RAD Project: Excerpt from Results

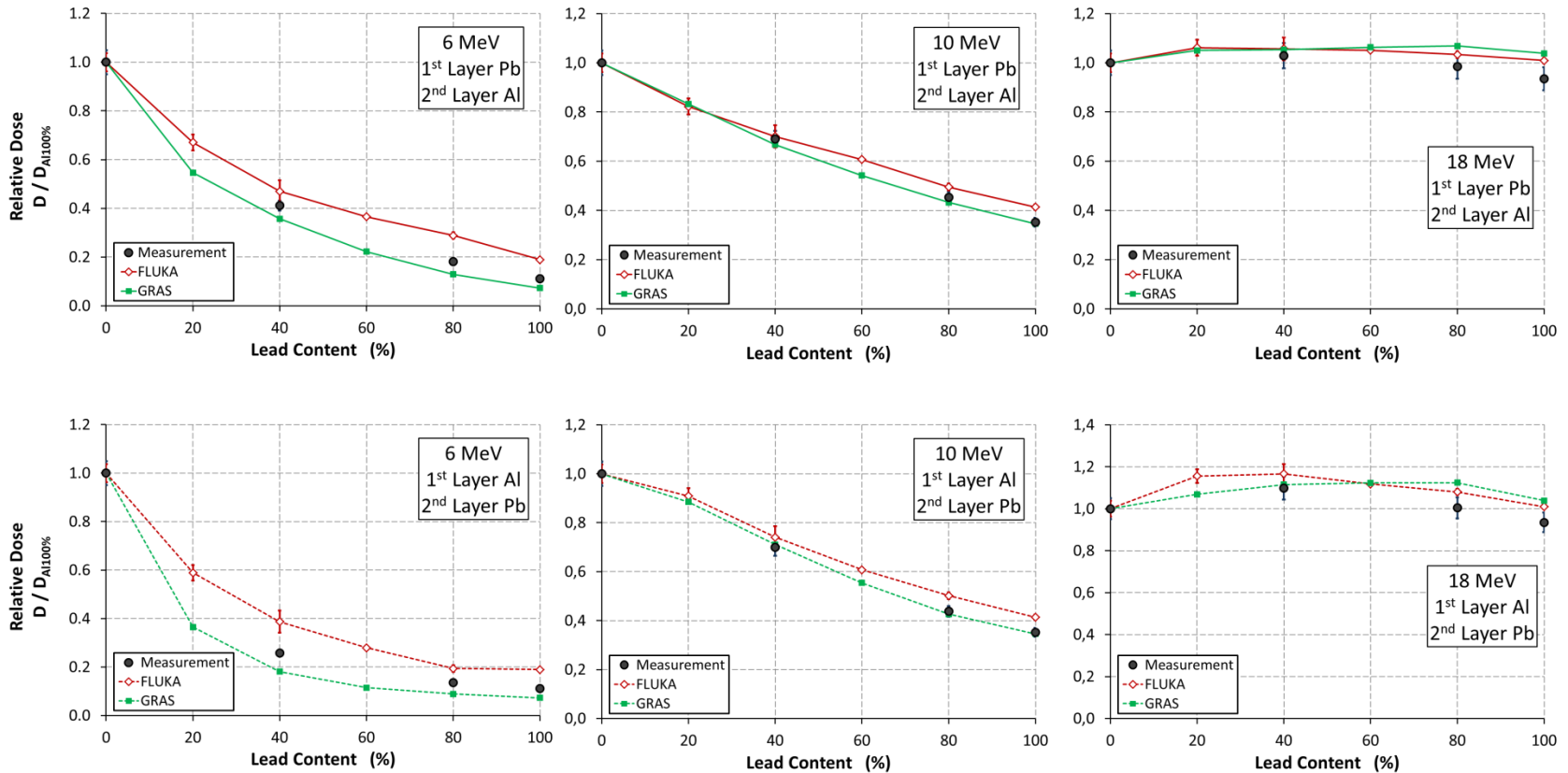
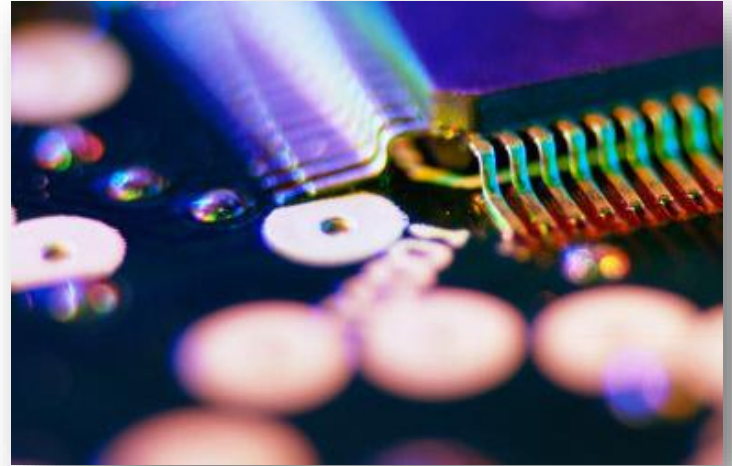


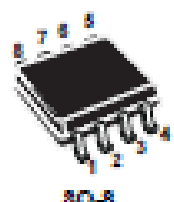



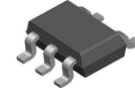

Figure : Comparison of experimental data and numerical data obtained with Monte Carlo codes FLUKA and GRAS. Y-axis shows the relative values (normalized to value for pure Aluminium shielding) of dose recorded in an Ionization chamber that is located directly behind a plane shielding. X-axis shows percentage of Lead content.

ECI Objectives

- To select and test European Commercial Off The Shelf (COTS) EEE components regarding Radiation Hardness Assurance according ESA standards
- To assess whether the tested components pass test requirements specified for space



ECI Candidates for Testing

Part	Description	Manufacturer	RHA-Test	
STS3P6F6	p-channel Power MosFET, V_{DS} : -60 V, I_D : -3 A	STM	TID	
			SEGR	
SPD04P10P G	SIPMOS p-channel Power MosFET, V_{DS} : -100 V, I_D : -4 A	Infineon	TID	
			SEGR	
TS331LT	Comparator	STM	TID	
TS3011ILT	Comparator	STM	TID	
AS1976-T	Comparator	AMS	TID	
LM2904DT	Op-Amp	STM	TID	

ECI TID Testing: Experiment conditions

- **Co-60 TID** radiation facility, Seibersdorf - EN/ISO IEC 17025 Accredited Test Lab
- **Sample size:** 5 biased, 5 unbiased, 2 control devices
- **Test standard:** ESA/SSC Basic Specification 22900
- **Annealing:** 24 hours room temperature, 168 hours 100°C

Electrical Parameter	Symbol	Unit
Drain-source Breakdown Voltage	$V_{BR(DSS)}$	V
Gate Threshold Voltage	V_{GS}	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	Ω
Inverse Diode Forward Voltage	V_{SD}	V
Reverse Gate-Source Leak Current	$I_{GSS(R)}$	A
Forward Gate-Source Leak Current	$I_{GSS(F)}$	A
Forward Transconductance*	g_{fs}	S

Parameters measured

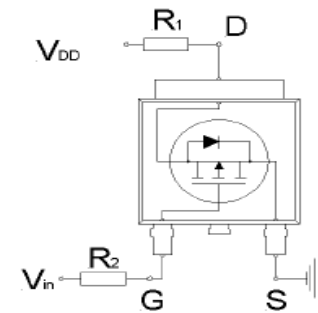


Co-60 TID Radiation Exposure Facility
EN/ISO IEC 17045 Test Lab, Seibersdorf

ECI TID Test Circuit (biased, unbiased), PCB Set-Up

SPD04P10G

Schematic of Test Circuitry



Biased

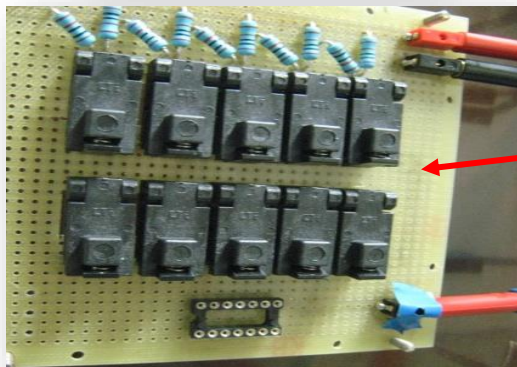
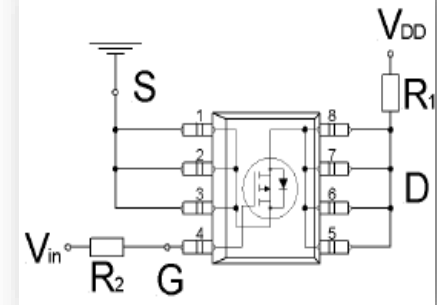
V_{DD} : 50V
 V_{in} : -20V
 Resistors: R_1 : 2k Ω , R_2 : 10 k Ω

Unbiased

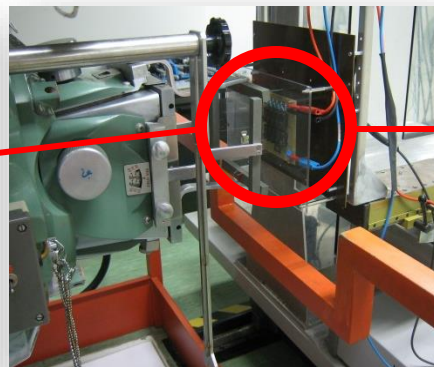
All terminals grounded; pin to ground resistance typically < 4 Ω

STS3PF6

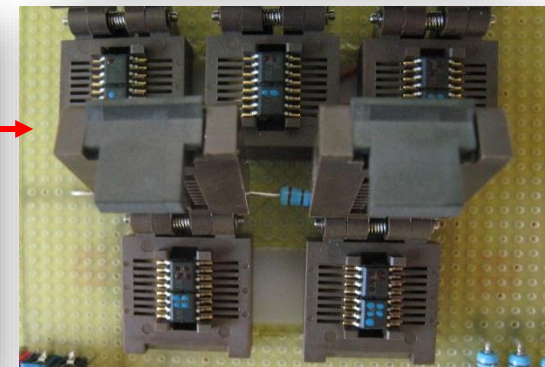
Schematic of Test Circuitry



PCB: biased / unbiased TID test (SPD04P10G)



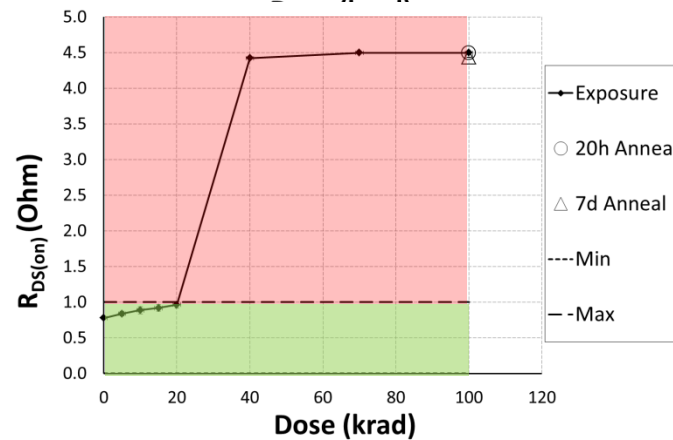
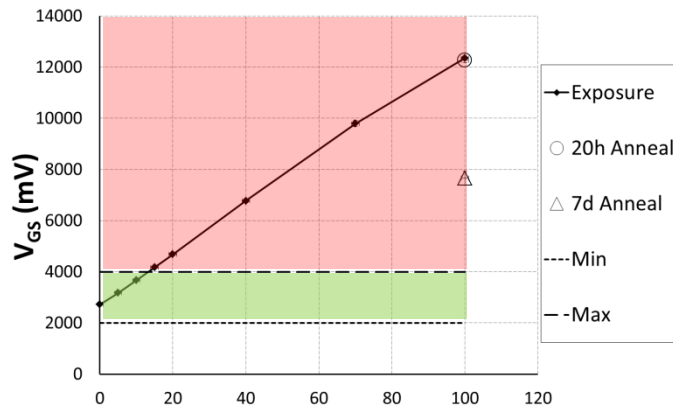
Co-60 Radiation Exposure Seibersdorf



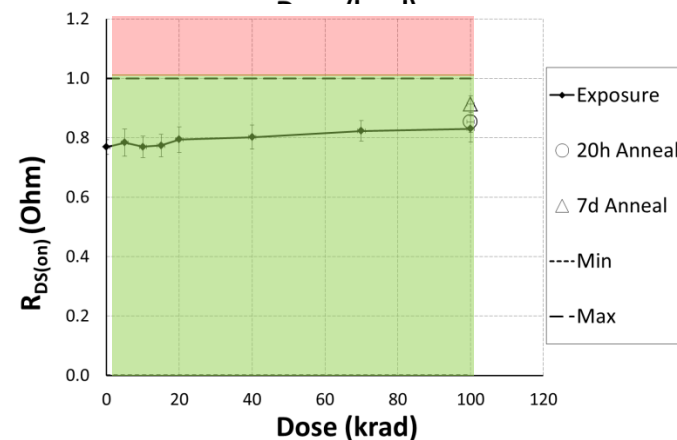
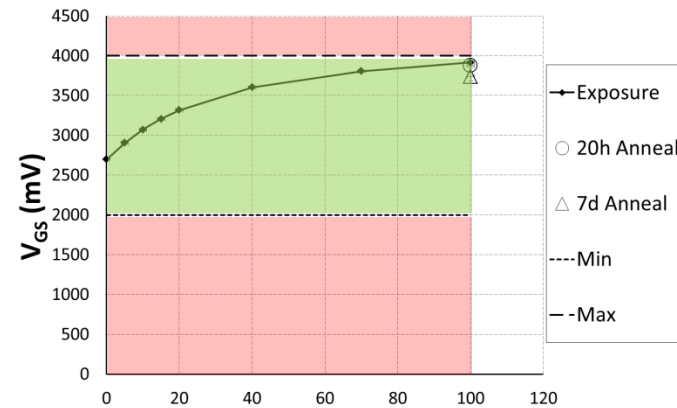
PCB: biased / unbiased TID test (STS3PF6)

ECI TID Test Results: SPD04P10G

BIASED

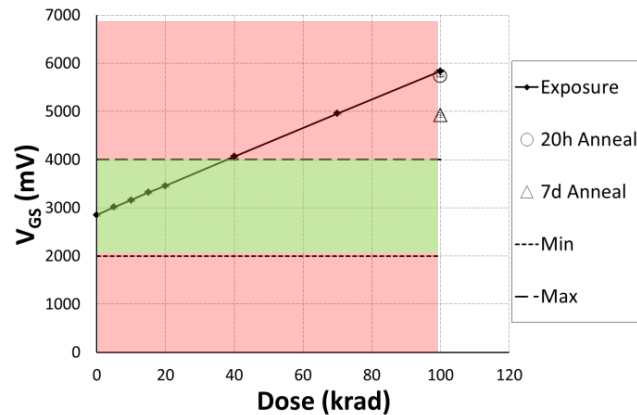


UNBIASED

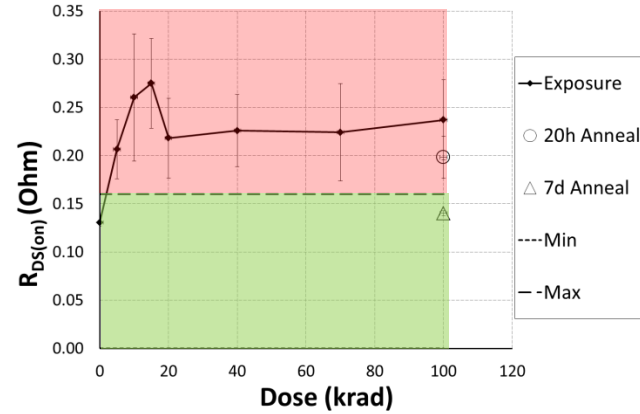
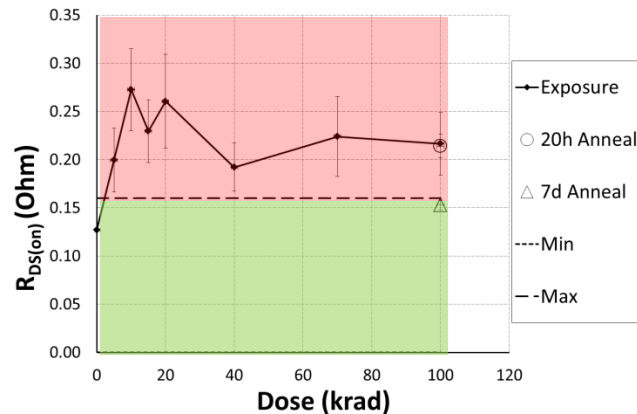
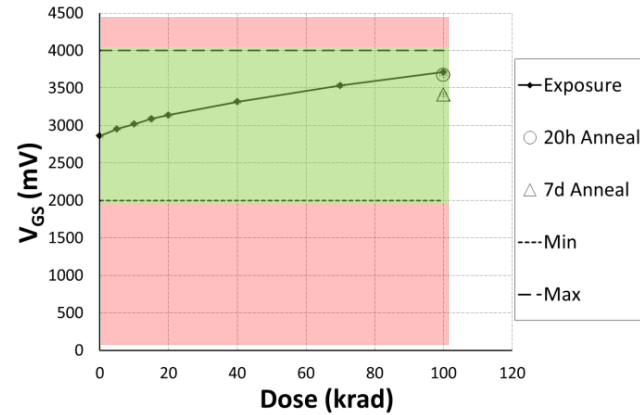


ECI TID Test Results: STS3PF6

BIASED



UNBIASED



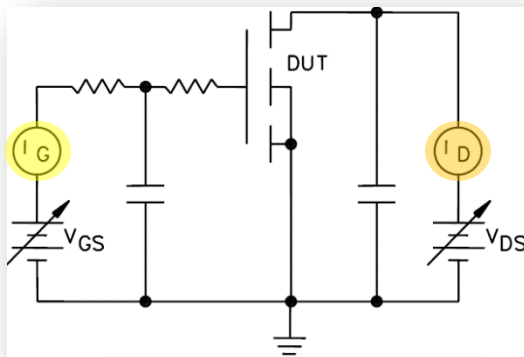
Parameters	Symbol	Unit	SPD04P10G		STS3PF6	
			Biased	Unbiased	Biased	Unbiased
Drain-source Breakdown Voltage	$V_{BR(DSS)}$	V	100 krad	100 krad	100 krad	100 krad
Gate Threshold Voltage	V_{GS}	V	15 krad	100 krad	40 krad	100 krad
Static Drain-Source On-Resistance	$R_{DS(on)}$	Ω	40 krad	100 krad	5 krad	5 krad
Inverse Diode Forward Voltage	V_{SD}	V	10 krad	5 krad	10 krad	15 krad
Reverse Gate-Source Leak Current	$I_{GSS(R)}$	A	100 krad	100 krad	100 krad	100 krad
Forward Gate-Source Leak Current	$I_{GSS(F)}$	A	100 krad	100 krad	100 krad	100 krad
Forward Transconductance	g_{fs}	S	40 krad	100 krad		

PASS

FAIL

SEGR Test Plan for STS3P6F6 and SPD04P10P

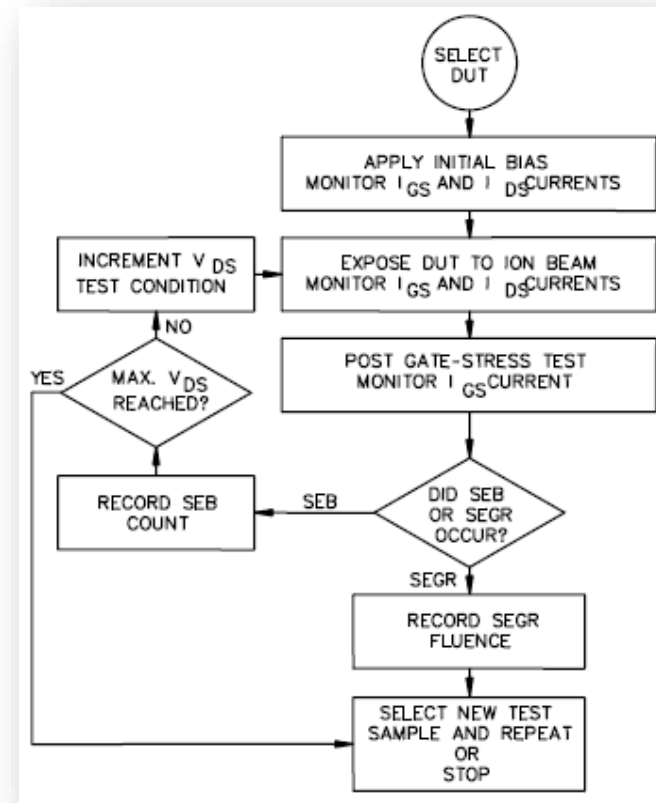
Schematic Test Circuit
(MIL-STD-750-1 Method 1080.1)



STS3P6F6 with and without lid

SPD04P10P prior and after etching

Characterization Flow Chart
(MIL-STD-750-1 Method 1080.1)

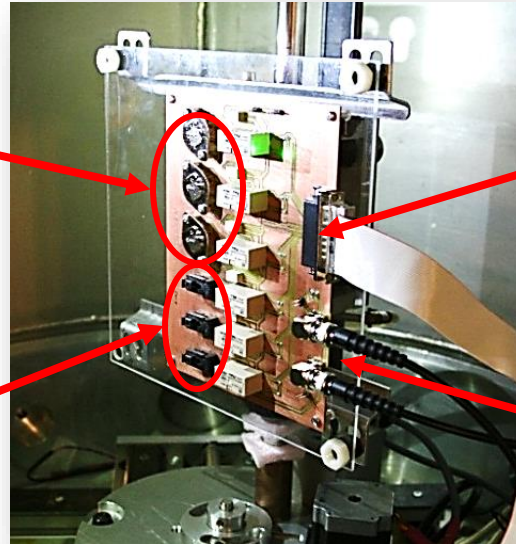
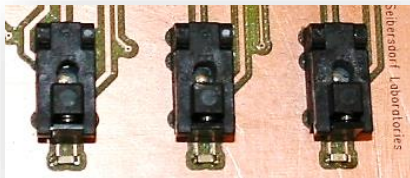


SEGR Test Set-Up at RADEF

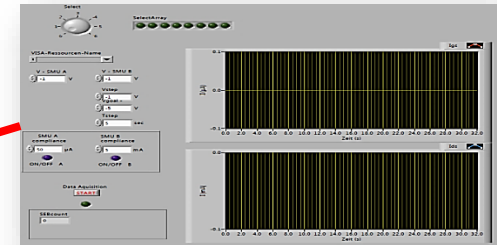
STS3PF6



SPD04P10G



LabVIEW: Relays, measurements



Test board mounted inside RADEF's vacuum chamber

Keithley 2612 dual source meter

Sample Size	27 devices per part type, 3 sample devices for each exposure sequence		
Parameters	V_{GS} : 0, 5, 10 V	V_{DS} : -50 V, ..., -100 V (SDP04P10P); -30 V, ..., -60 V (STS3PF6)	
LET (MeV cm² mg⁻¹)	18.5	32.1	60
Heavy ions, energy	Fe / 523 MeV	Kr / 768 MeV	Xe / 1.2 GeV
Average Flux (cm⁻² s⁻¹)	$1.09 \cdot 10^4$	$1.18 \cdot 10^4$	$7.27 \cdot 10^3$
Fluence (cm⁻²)	$3 \cdot 10^5$		

SEGR Results: Safe Operating Area – SOA (SF=1)

	SPD04P10P G										STS3P6F6										
LET (MeV/mg/cm ²)	18.5			32.1			60				18.5			32.1			60				
	V _{GS} (V)			V _{GS} (V)			V _{GS} (V)				V _{GS} (V)			V _{GS} (V)			V _{GS} (V)				
V _{DS} (V)	0	5	10	0	5	10	0	5	10	15	0	5	10	0	5	10	0	5	10	15	20
-100	Green	Green	Green	Green	Green	Red	Red	Red	Red	Red											
-90	Green	Green	Green	Green	Green	Red	Red	Red	Red	Red											
-80	Green	Green	Green	Green	Green	Green	Red	Red	Red	Red											
-70	Green	Green	Green	Green	Green	Green	Red	Red	Red	Red											
-60	Green	Green	Green	Green	Green	Green	Red	Red	Red	Red	Green	Grey	Grey	Green	Grey	Grey	Red	Grey	Grey	Grey	Grey
-55	Green	Green	Green	Green	Green	Green	Green	Red	Red	Red	Red	Green	Green	Grey	Green	Red	Red	Red	Red	Red	Grey
-50	Green	Green	Green	Green	Green	Green	Green	Red	Red	Red	Red	Green	Green	Red	Green	Green	Red	Red	Red	Red	Red
-40	Green	Green	Green	Green	Green	Green	Green	Green	Green	Red	Red	Green	Green	Green	Green	Red	Red	Red	Red	Red	Red
-30	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Red	Green	Green	Green	Green	Red	Green	Red	Red	Red	Red
-25	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Red	Green	Green	Green	Green	Green	Green	Red	Red	Red	Red
-20	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Red	Red	Red
-15	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Red	Red
-10	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Green	Red

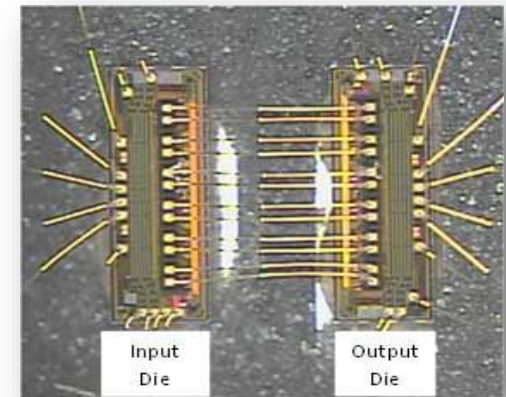
CONTENT

1. Project Overview ECI-SL-01 – Testing of Commercial Components
2. ECI-SL-01 candidates selected for testing
3. Results TID-Testing
4. Results SEGR-Testing
5. Project Overview REDI – Radiation Evaluation of Digital Isolators
6. REDI candidates selected for testing

Overview: REDI- Radiation Evaluation of Digital Isolators

Objectives

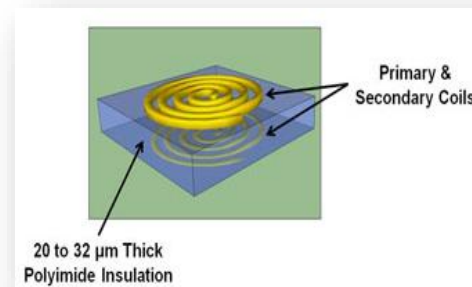
- Identify currently available commercial digital isolators for applications in space missions, specifically the JUICE mission, as replacement for optocouplers
- Perform detailed radiation evaluation (TID and SEE) of the selected digital isolators.



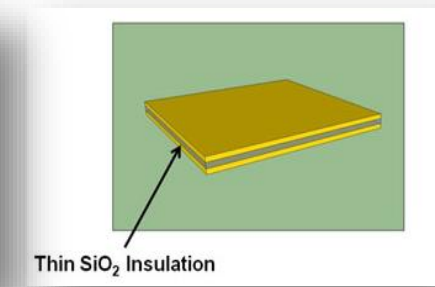
De-capsulated digital isolator
Courtesy: Silicon Labs

Digital Isolators

- CMOS technology
- Magnetic or Capacitive Coupling
- Polyimide or SiO₂ insulation



Transformer with polyimide insulation



Capacitor with SiO₂ insulation

Courtesy: Analog Devices

REDI Candidates Selected for Testing

Manufacturer	Texas Instruments	Texas Instruments	Silicon Labs	Analog Devices	Analog Devices	Maxim Integrated
Investigated Part	ISO15DW	ISO7220MDR	SI8261ACC-C-IP	ADUM1201ARZ	ADUM1100URZ	MAX14850ASE+
Technology	capacitive-coupling bulk CMOS	capacitive-coupling bulk CMOS	capacitive-coupling bulk CMOS	monolithic transformer high speed bulk CMOS	monolithic transformer high speed bulk CMOS	capacitive-coupling BiCMOS
Package Type	SOIC	SOIC	DIP	SOIC	SOIC-8	SOIC
Min Voltage / V	3,15	3,0	5,0	2,7	3,0	3,0
Max Voltage / V	3,6	5,5	30,0	5,5	5,5	5,5
Prop Delay / ns	340	16	40	150	11	7

REDI Test Plan

TID-Testing

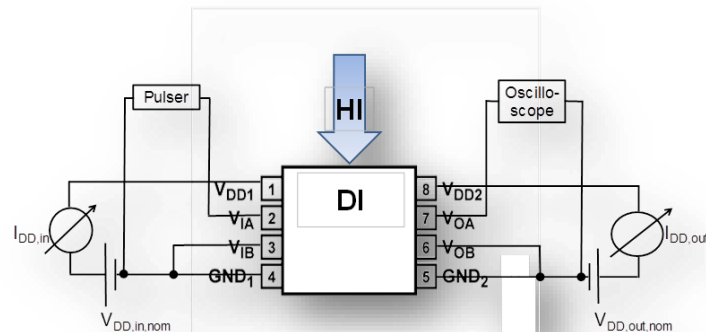
- Source: Co-60, electrons (JUICE mission)
- Parameter: Supply currents of i/p and o/p; isolation performance; Input Current; Output voltages at High and Low logic

SEE-Testing

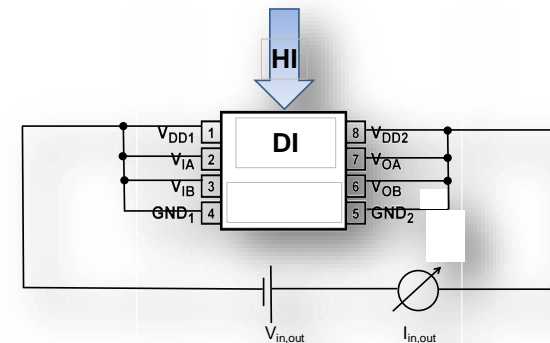
- SET and SEL, Single Event Dielectric Isolation Rapture (SEDIR)
- SEE testing for LETs between 4 - 55 MeV/mg/cm² (e.g. Ne, Si, Ar, Kr and Xe)

DD-Testing

- neutrons



Sketch of a combined heavy ion SET and SEL test

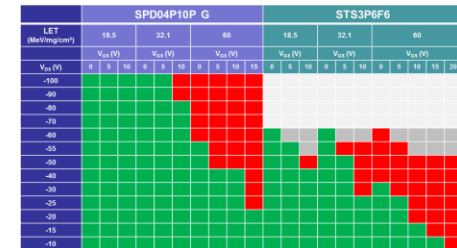


Sketch of a heavy ion SEDIR test

Summary and Conclusions

ECI – Power MOSFETS: SPD04P10P, STS3PF6

- We carried out **TID** and **SEGR** radiation tests of two **Power MosFET's** from **STM** and **Infineon** according ESA and MIL standards
- TID**: maximum dose $D(\text{Si}) = 1\text{kGy (100 krad)}$; **SEGR**: LET: 18.5 - 60 MeV cm² mg⁻¹
- TID** testing for both components, biased and unbiased passed for doses $D(\text{Si}) < 5\text{krad}$.
- For larger doses, almost all parameters showed degradation for both components, biased and unbiased; just the three parameters: $V_{\text{BR(DSS)}}$, $I_{\text{GSS(R)}}$, and $I_{\text{GSS(F)}}$ passed for **1kGy (100krad)** radiation testing.
- SEGR** tests showed for tested LET range **SOA (SF=1)** for:
 - **SPD04P10P G**: $V_{\text{DS}} = 0 \dots -20\text{ V}$, $V_{\text{GS}} = 15\text{V}$. $V_{\text{DS}} = 0 \dots -55\text{ V}$, $V_{\text{GS}} = 0\text{V}$
 - **STS3P6F6**: $V_{\text{DS}} = 0 \dots -10\text{ V}$, $V_{\text{GS}} = 15\text{V}$. $V_{\text{DS}} = 0 \dots -30\text{ V}$, $V_{\text{GS}} = 0\text{V}$



REDI – Radiation Evaluation of Digital Isolators

- 3 candidates for testing, different manufacturers and technologies were identified and selected
- Experiments for **TID** in progress
- Test plans for **SEE/SEL** and **SEDIR** are under preparation

Secondments

- **Business and Administration Secondment, IBA Dosimetry**
 - 2-week training period (16 – 27 February 2015), Supervision of Mr. Salih Arican, Senior Product Manager.
 - Business-domain: Radiotherapy solutions, emphasis on Daily Quality Assurance activities.
 - Competition analyses for Daily Quality Assurance solutions, Market assessment, Financial calculations for profitability/viability of Product for a Positioning paper
- **Scientific Secondment, R2E Group (Radiation to Electronics) CERN**
 - Familiarization with Single Event Transient and Single Event Latchup experiments. Supervision: Dr. Markus Brugger, Mr. Salvatore Danzeca
 - Digital Isolator Experiments...
 - Outcome- Test plan draft for SET and SEL experiments.

Acknowledgements

- **ARDENT**, Marie Curie Early Initial Training Network Fellowship of the European Community's Seventh Framework Programme under contract number (PITN-GA-2011-289198-ARDENT)
- Radiation Hardness Assurance and Space Weather Group at Seibersdorf Laboratories: Dr. Michael Wind, DI. Marcin Latocha and Dr. Peter Beck for guidance in all activities.
- Dr. Markus Stock and Dr. Georg Dietmar for support in experiments at AKH, Vienna.

Work was carried out in projects contracted by **ESA** under contracts:

e²RAD: ESA – C# 4000108163/13/NL/SC/fk

ECI: ESA C# 4000108163/13/NL/SC/fk

REDI: ESA C# 4000112480/14/NL/SW.



Thank you for your attention!

